

Abstract of the Disclosure

The present invention relates to a method for fabricating an image sensor capable of improving a dark
5 current characteristic. The method includes the steps of:
forming sequentially a pad oxide layer and a pad nitride
layer on a substrate and selectively removing the pad oxide
layer and the pad nitride layer to expose a surface of the
substrate in which a field insulation layer will be formed;
10 forming the field insulation layer by performing a channel
stop ion-implantation process to the exposed substrate with
use of the pad nitride layer as a mask; removing a partial
portion of the pad nitride layer so that one side of the
pad nitride layer is spaced out with a predetermined
15 distance from an edge of the field insulation layer; and
performing an additional ion-implantation process onto the
exposed substrate surface and the field insulation layer by
using the pad nitride layer as a mask.